

TRANSISTOR (PNP)

FEATURES

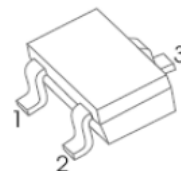
- General Purpose Amplifier Applications

MARKING: 2GM

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

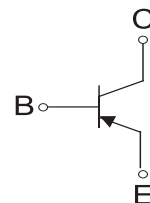
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	833	$^{\circ}\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

SOT-323



1. BASE
2. EMITTER
3. COLLECTOR

Equivalent Circuit



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB}=-80\text{V}, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-60\text{V}, I_B=0$			-1	μA
Emitter-base breakdown voltage	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100		400	
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE}=-1\text{V}, I_C=-100\text{mA}, f=100\text{MHz}$	50			MHz

Typical Characteristics

